ABSTRACT

DUAL SILICON-ON-INSULATOR DEVICE WAFER DIE

A silicon-on-insulator semiconductor device [46] and manufacturing method therefor is provided in which a single wafer die [10] contains a transistor over an insulator layer [14] to form a fully depleted silicon-on-insulator device [46] and a transistor formed in a semiconductor island [26''] over an insulator structure [24] on the semiconductor wafer forms a partially depleted silicon-on-insulator device [48].

FIGURE 10